

MPS6516 thru' MPS6519 are PNP silicon planar epitaxial transistors designed for general purpose amplifier applications and for complementary circuitry.

CASE TO-92A



ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage
 Collector-Base Voltage
 Emitter-Base Voltage
 Collector Current
 Total Power Dissipation @ $T_A=25^{\circ}\text{C}$
 @ $T_C=25^{\circ}\text{C}$
 Operating Junction & Storage Temperature

	MPS6516/7/8	MPS6519
V _{CEO}	40V	25V
V _{CB0}	40V	25V
V _{EB0}	4V	4V
I _C	100mA	100mA
P _{tot}	350mW	350mW
	1W	1W
T _j , T _{stg}	-55 to +150°C	

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	BV _{CEO}	40			V	I _C =0.5mA I _B =0
Emitter-Base Breakdown Voltage	BV _{EB0}	4			V	I _E =10μA I _C =0
Collector Cutoff Current	IC _{B0}			50	nA	V _{CB} =30V I _E =0
				50	nA	V _{CB} =20V I _E =0
Collector Cutoff Current	IC _{B0}			1	μA	T _A =60°C V _{CB} =30V I _E =0
				1	μA	V _{CB} =20V I _E =0
Collector-Emitter Saturation Voltage	V _{CE(SAT)}			0.5	V	I _C =50mA I _B =5mA
D.C. Current Gain	H _{FE}	50		100		I _C =2mA V _{CE} =10V
		90		180		
		150		300		
		250		500		
D.C. Current Gain	H _{FE} *	30				I _C =100mA V _{CE} =10V
		60				
		90				
		150				
Current Gain-Bandwidth Product	f _T		150		MHz	I _C =2mA V _{CE} =10V
			250		MHz	I _C =10mA V _{CE} =10V

5.80 * Pulse Test : Pulse Width=0.3ms, Duty Cycle=1%



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ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Output Capacitance	Cob			4	pF	V _{CB} =10V IE=0 f=100kHz
Noise Figure	NF		2		dB	I _C =10 μ A V _{CE} =5V R _S =10K Ω Power Bandwidth =15.7KHz, 3dB points @ 10Hz & 10kHz

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